

ETCHING METHOD

ABSTRACT

Disclosed herein is an etching method for a workpiece. The etching method includes the steps of dissociating an inert gas to form a plasma in an evacuated condition of a chamber to thereby remove moisture present on the workpiece set in the chamber, and next dissociating a fluorine-based stable gas instead of the inert gas to form a plasma in the chamber after removing the moisture to thereby dry-etch the workpiece.

(Fig. 2A)